

This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	720	LDMOSS\$2 or LD-MOSS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
2	BRS	L2	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
3	BRS	L3	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
4	BRS	L4	479	LDDMOSS\$2 or LDD-MOSS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
5	BRS	L5	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
6	BRS	L6	178	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
7	BRS	L7	250	lateral\$4 near7 (metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8	BRS	L8	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
9	BRS	L9	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
10	BRS	L10	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
11	BRS	L11	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58			0
12	BRS	L12	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59			0
13	BRS	L13	9374	1 or 2 or 3 or 4 or 5 or 6 or 7 or 8 or 9 or 10 or 11 or 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:03			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
14	BRS	L14	43547	(amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44			0
15	BRS	L15	334	13 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:06			0
16	BRS	L16	5148	implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:13			0
17	BRS	L17	43678	(silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09			0
18	BRS	L22	25985	implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:22			0
19	BRS	L23	7645	implant\$8 with 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:24			0
20	BRS	L24	26134	16 or 22 or 23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
21	BRS	L25	176	24 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25			0
22	BRS	L26	152356	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:36			0
23	BRS	L27	141012	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:37			0
24	BRS	L28	120	25 and 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38			0
25	BRS	L29	109	26 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38			0
26	BRS	L30	1255	24 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44			0
27	BRS	L31	280	30 and (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:45			0

	Type	L #	Hits	Search Text	Dbs	Time Stamp	Comments	Error Definition	Errors
28	BRS	L32	172	26 and 27 and 31	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:46			0
29	BRS	L33	280	25 or 31	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:54			0
30	BRS	L34	848	24 with (amorphous or amorph\$9) with (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:57			0
31	BRS	L35	45	34 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:57			0
32	BRS	L36	1853	24 same (amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:58			0
33	BRS	L37	78	36 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:58			0
34	BRS	L38	43237	(crystal1\$9 or re-crystal1\$9 or (re adj crystal1\$9)) with amorph\$9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:53			0

	Type	L #	Hits	Search Text	Dbs	Time Stamp	Comments	Error Definition	Error
35	BRS	L39	8629	gaussian with (distributed\$6 or profil\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:55			0
36	BRS	L40	3	35 and 38 and 39	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:56			0
37	BRS	L41	3	37 and 38 and 39	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:56			0
38	BRS	L42	6	33 and 38 and 39	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:58			0
39	BRS	L43	25	35 and 38	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:59			0
40	BRS	L44	35	37 and 38	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 21:59			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
2	BRS	L2	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
3	BRS	L3	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
4	BRS	L4	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
5	BRS	L5	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
6	BRS	L6	178	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
7	BRS	L7	250	lateral\$4 near\$7 (metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8 BRS	L8	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
9 BRS	L9	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
10 BRS	L10	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
11 BRS	L11	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58			0
12 BRS	L12	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59			0
13 BRS	L13	9374	1 or 2 or 3 or 4 or 5 or 6 or 7 or 8 or 9 or 10 or 11 or 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:03			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
14	BRS	L14	43547	(amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44			0
15	BRS	L15	334	13 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:06			0
16	BRS	L16	5148	implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:13			0
17	BRS	L17	43678	(silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09			0
18	BRS	L22	25985	implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:22			0
19	BRS	L23	7645	implant\$8 with 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:24			0
20	BRS	L24	26134	16 or 22 or 23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
21	BRS	L25	176	24 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25			0
22	BRS	L26	152356	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:36			0
23	BRS	L27	141012	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:37			0
24	BRS	L28	120	25 and 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38			0
25	BRS	L29	109	26 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38			0
26	BRS	L30	1255	24 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44			0
27	BRS	L31	280	30 and (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:45			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
28	BRS	L32	172	26 and 27 and 31	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:46			0
29	BRS	L33	280	25 or 31	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:54			0
30	BRS	L34	848	24 with (amorphous or amorph\$9) with (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:57			0
31	BRS	L35	45	34 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:57			0
32	BRS	L36	1853	24 same (amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:58			0
33	BRS	L37	78	36 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 19:58			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
2	BRS	L2	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
3	BRS	L3	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
4	BRS	L4	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
5	BRS	L5	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
6	BRS	L6	178	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
7	BRS	L7	250	lateral\$4 near7 (metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8	BRS	L8	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
9	BRS	L9	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
10	BRS	L10	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
11	BRS	L11	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58			0
12	BRS	L12	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59			0
13	BRS	L13	9374	1 or 2 or 3 or 4 or 5 or 6 or 7 or 8 or 9 or 10 or 11 or 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:03			0

	Type	L #	Hits	Search Text	Dbs	Time Stamp	Comments	Error Definition	Errors
14	BRS	L14	43547	(amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44			0
15	BRS	L15	334	13 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:06			0
16	BRS	L16	5148	implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:13			0
17	BRS	L17	43678	(silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09			0
18	BRS	L22	25985	implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:22			0
19	BRS	L23	7645	implant\$8 with 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:24			0
20	BRS	L24	26134	16 or 22 or 23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
21 BRS	L25	176	24 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25			0
22 BRS	L26	152356	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:36			0
23 BRS	L27	141012	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:37			0
24 BRS	L28	120	25 and 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38			0
25 BRS	L29	109	26 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38			0
26 BRS	L30	1255	24 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:44			0
27 BRS	L31	280	30 and (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:45			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error Count
28	BRS	L32	172	26 and 27 and 31	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:46			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error
1	BRS	L1	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
2	BRS	L2	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55			0
3	BRS	L3	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
4	BRS	L4	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
5	BRS	L5	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
6	BRS	L6	178	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56			0
7	BRS	L7	250	lateral\$4 near\$7 (metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8	BRS	L8	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
9	BRS	L9	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
10	BRS	L10	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57			0
11	BRS	L11	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58			0
12	BRS	L12	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:59			0
13	BRS	L13	9374	1 or 2 or 3 or 4 or 5 or 6 or 7 or 8 or 9 or 10 or 11 or 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:03			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
14	BRS	L14	43547	(amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:05			0
15	BRS	L15	334	13 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:06			0
16	BRS	L16	5148	implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:13			0
17	BRS	L17	43678	(silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:09			0
18	BRS	L22	25985	implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:22			0
19	BRS	L23	7645	implant\$8 with 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:24			0
20	BRS	L24	26134	16 or 22 or 23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
21	BRS	L25	176	24 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:25			0
22	BRS	L26	152356	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:36			0
23	BRS	L27	141012	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:37			0
24	BRS	L28	120	25 and 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38			0
25	BRS	L29	109	26 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 18:38			0